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PATENT  
740756-1996

13/C  
7. Sept  
4/20/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:

Shunpei YAMAZAKI et al.

Application No.: 09/352,362

Filed: July 13, 1999

For: CRYSTALLINE SEMI-  
CONDUCTOR THIN FILM,  
METHOD OF FABRICATING  
THE SAME, SEMICONDUCTOR  
DEVICE, AND METHOD OF  
FABRICATING THE SAME

Art Unit: 2815

Examiner: J. R. Diaz

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on April 9, 2001.

Shirley B. Strawn

AMENDMENT

Commissioner of Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Examiner's non-final Office Action mailed November 9, 2000, the period for responding having been extended 2 months, please consider the following

amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claims 5-14, 27 and 29 without prejudice or disclaimer of any of the subject matter contained therein.

Please amend claims 15, 17, 20, 22, 25 and 28 as follows:

(Amended) A method of fabricating a semiconductor device including a thin film transistor, wherein the thin film transistor is formed through the steps of: